

## 800V N-Channel MOSFET

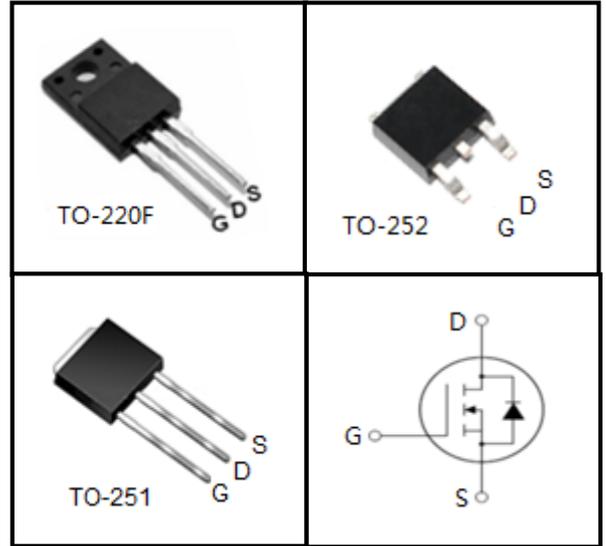


### FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

### APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
RS4N80F	TO-220F	RS4N80F
RS4N80M	TO-251	RS4N80M
RS4N80D	TO-252	RS4N80D

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted					
Parameter	Symbol	Value			Unit
		TO-220F	TO-252	TO-251	
Drain-Source Voltage ( $V_{GS} = 0V$ )	$V_{DSS}$	800			V
Continuous Drain Current	$I_D$	3			A
Pulsed Drain Current (note1)	$I_{DM}$	12			A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$			V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	160			mJ
Avalanche Current (note1)	$I_{AR}$	3			A
Repetitive Avalanche Energy (note1)	$E_{AR}$	20			mJ
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	25	70		W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150			$^\circ\text{C}$

Thermal Resistance					
Parameter	Symbol	Value			Unit
		TO-220F	TO-252	TO-251	
Thermal Resistance, Junction-to-Case	$R_{thJC}$	5	1.78		K/W
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62.5	60		

Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	800	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 800V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu A$
		$V_{DS} = 640V, V_{GS} = 0V, T_J = 125^\circ\text{C}$	--	--	100	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1.5A$	--	3	3.6	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0\text{MHz}$	--	793	--	$\mu F$
Output Capacitance	$C_{oss}$		--	63	--	
Reverse Transfer Capacitance	$C_{rss}$		--	9	--	
Total Gate Charge	$Q_g$	$V_{DD} = 640V, I_D = 3A,$ $V_{GS} = 10V$	--	19	--	nC
Gate-Source Charge	$Q_{gs}$		--	3	--	
Gate-Drain Charge	$Q_{gd}$		--	9	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 3A,$ $R_G = 25\Omega$	--	12	--	ns
Turn-on Rise Time	$t_r$		--	20	--	
Turn-off Delay Time	$t_{d(off)}$		--	30	--	
Turn-off Fall Time	$t_f$		--	45	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	3	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	12	
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 3A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	$t_{rr}$	$V_{GS} = 0V, I_S = 3A,$ $di_F/dt = 100A/\mu s$	--	300	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	2.6	--	$\mu C$

### Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_{AS} = 3A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width  $\leq 300\mu s$ , Duty Cycle  $\leq 1\%$

Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )

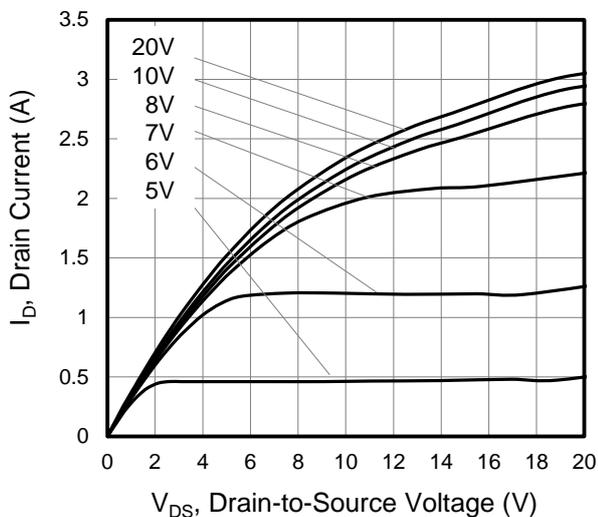


Figure 2. Body Diode Forward Voltage

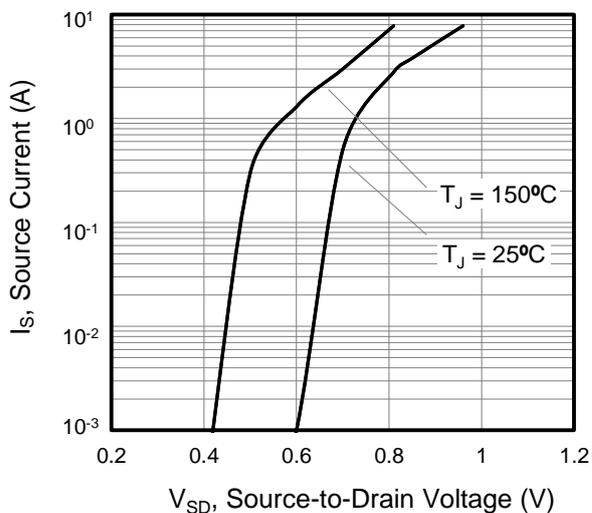


Figure 3. Drain Current vs. Temperature

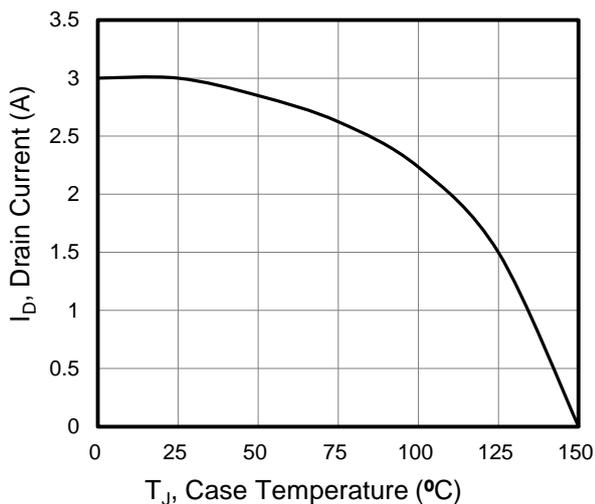


Figure 4.  $BV_{DSS}$  Variation vs. Temperature

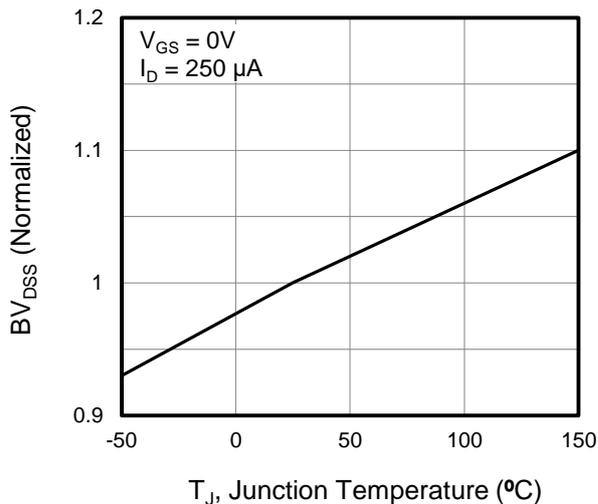


Figure 5. Transfer Characteristics

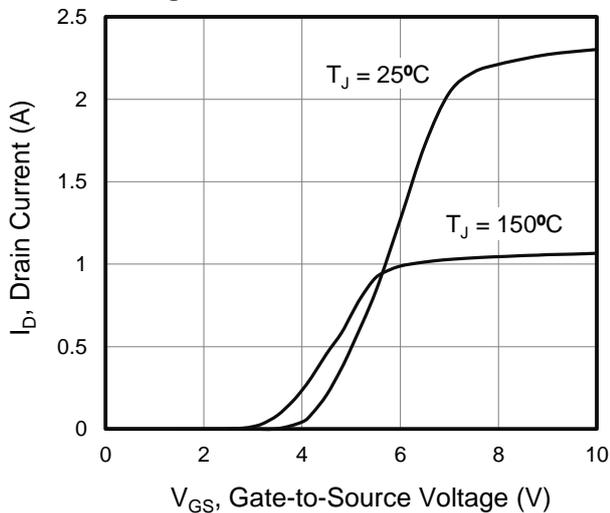
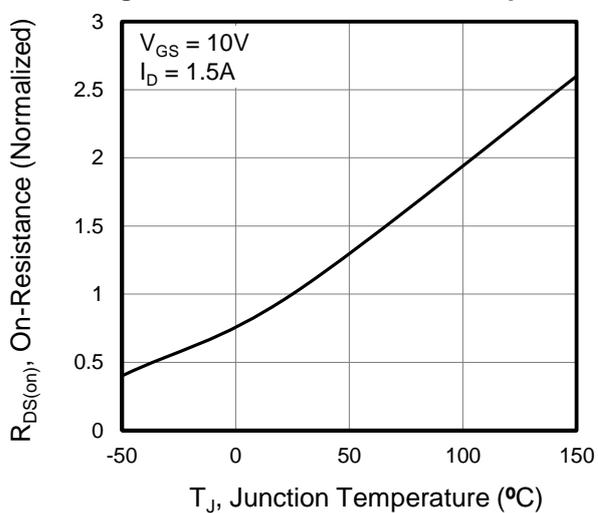


Figure 6. On-Resistance vs. Temperature



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. Capacitance

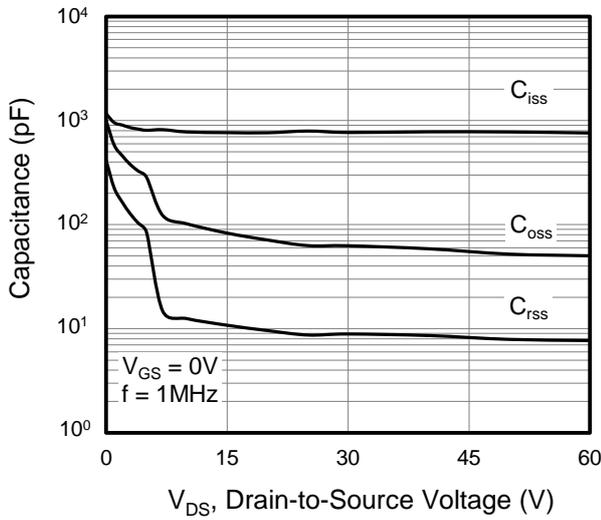


Figure 8. Gate Charge

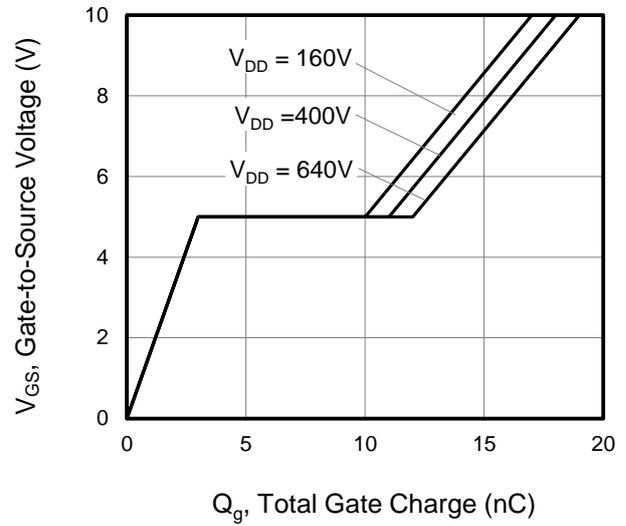


Figure 9. Transient Thermal Impedance

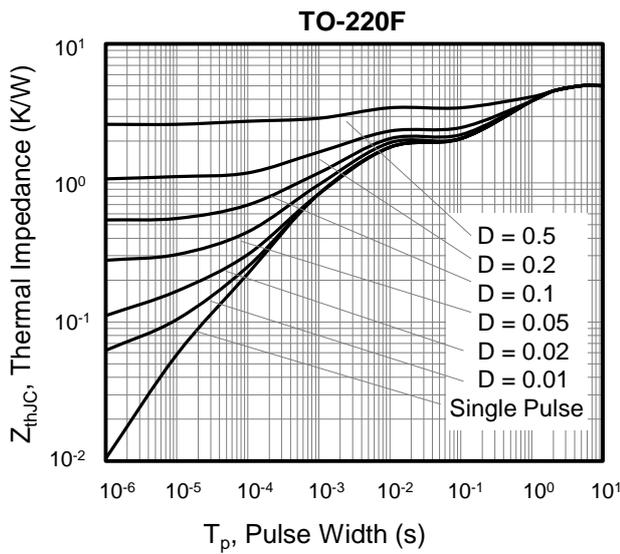
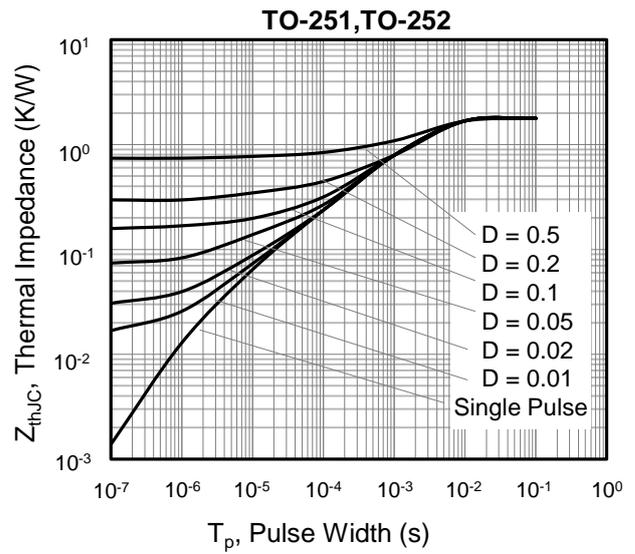
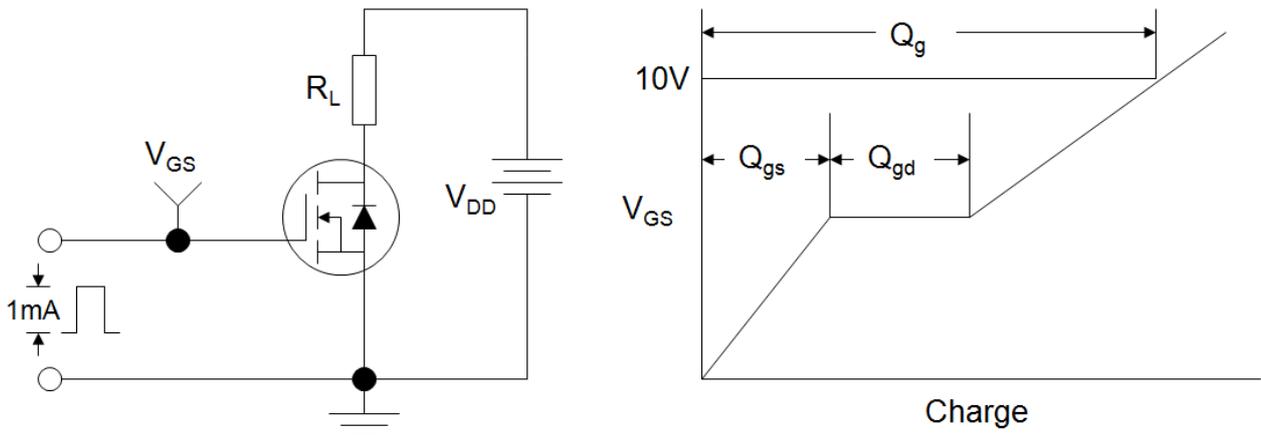


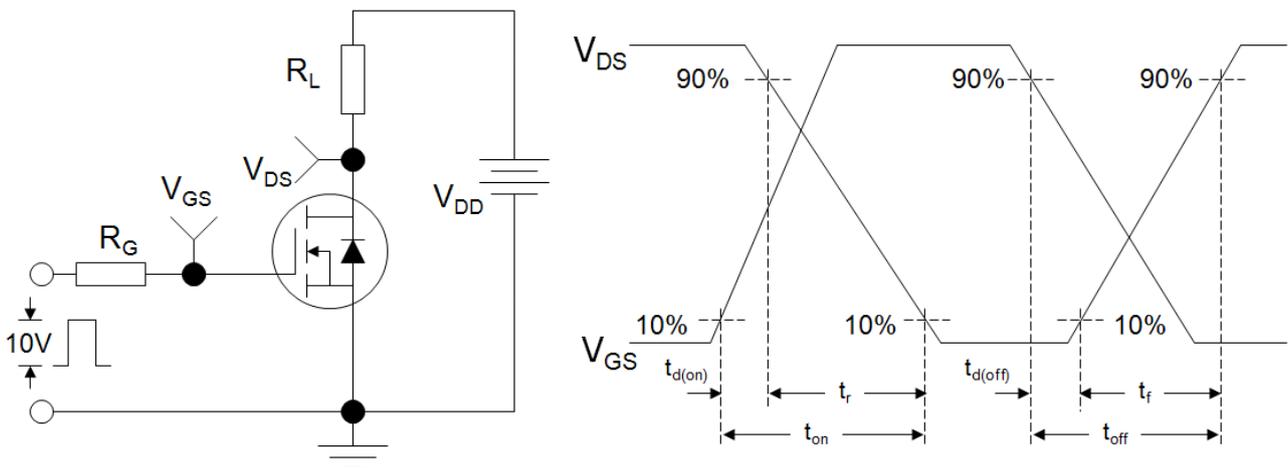
Figure 10. Transient Thermal Impedance



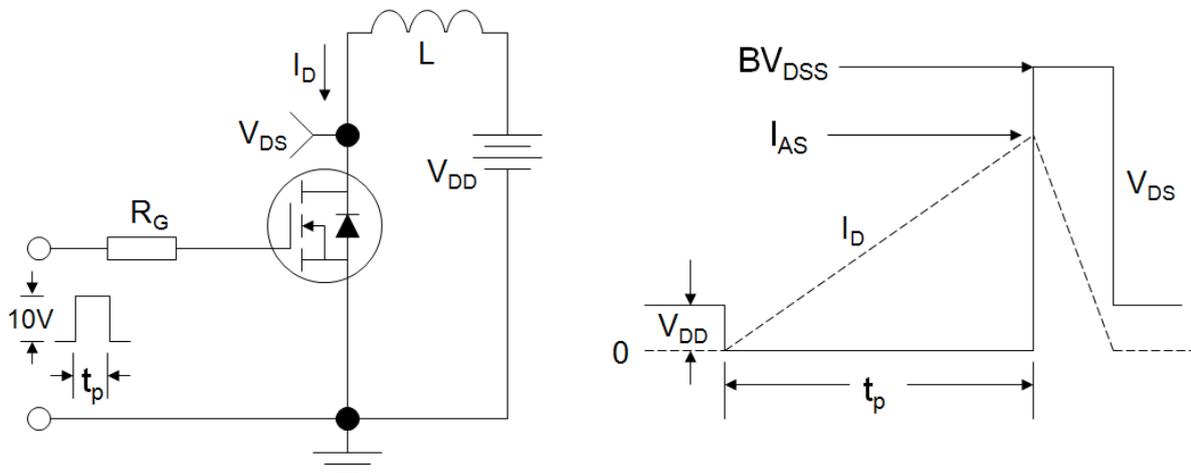
**Figure A: Gate Charge Test Circuit and Waveform**



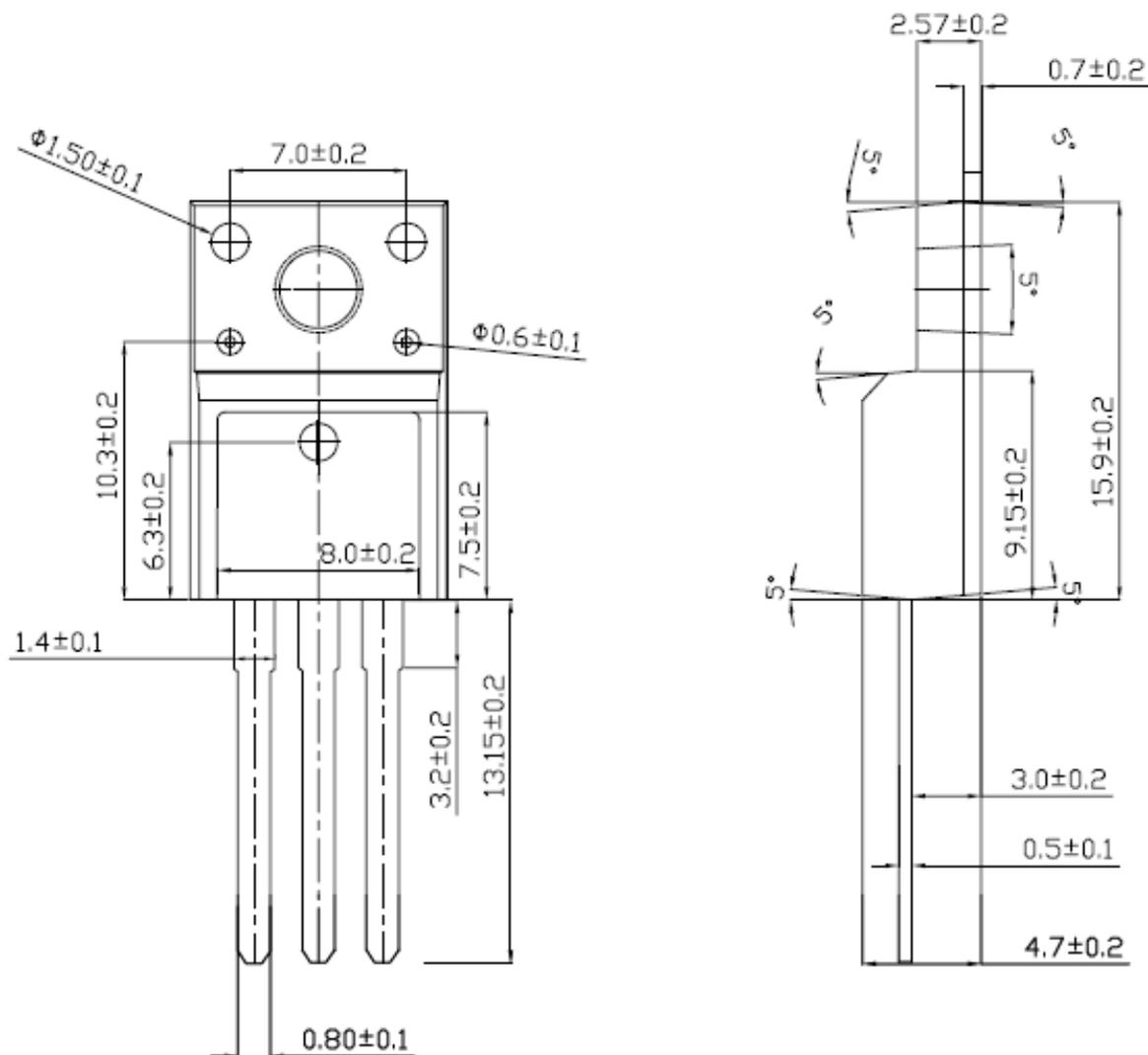
**Figure B: Resistive Switching Test Circuit and Waveform**



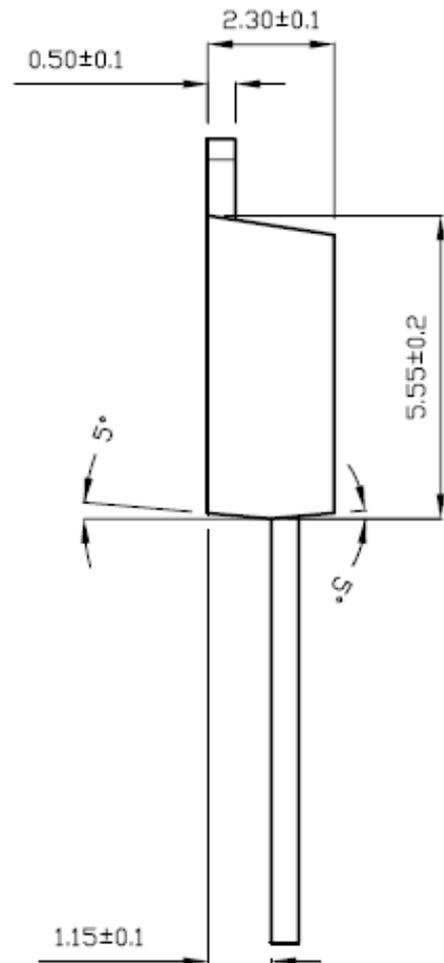
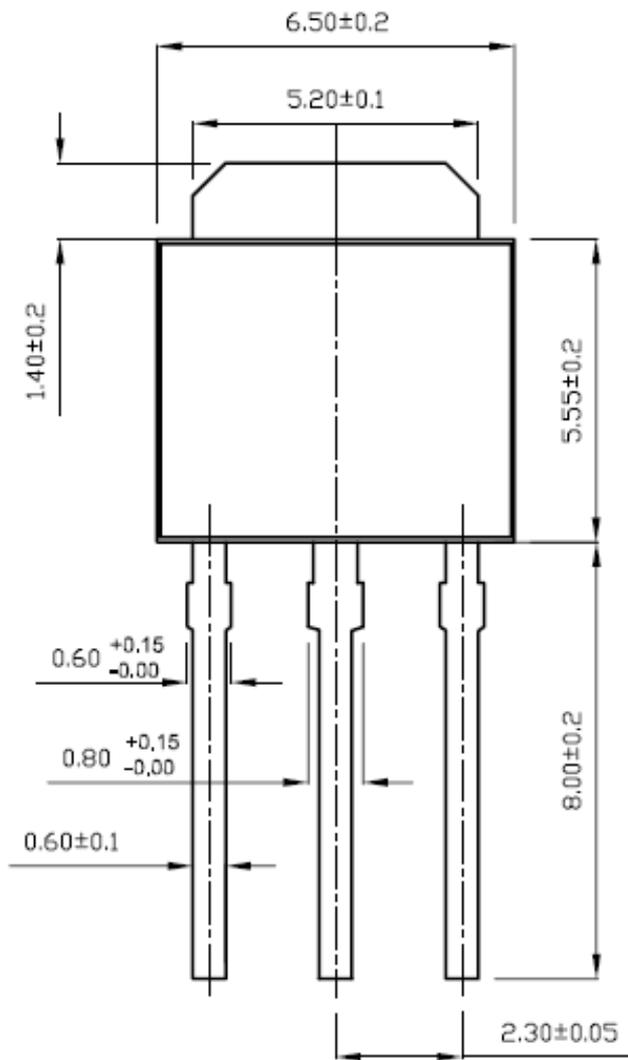
**Figure C: Unclamped Inductive Switching Test Circuit and Waveform**



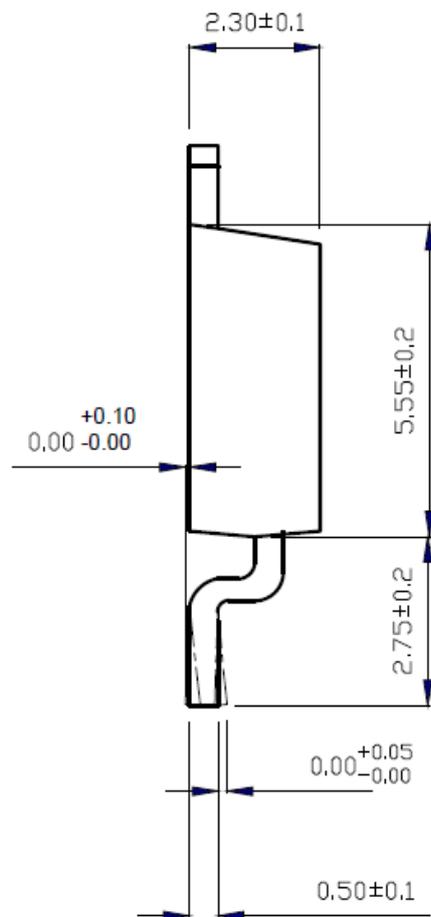
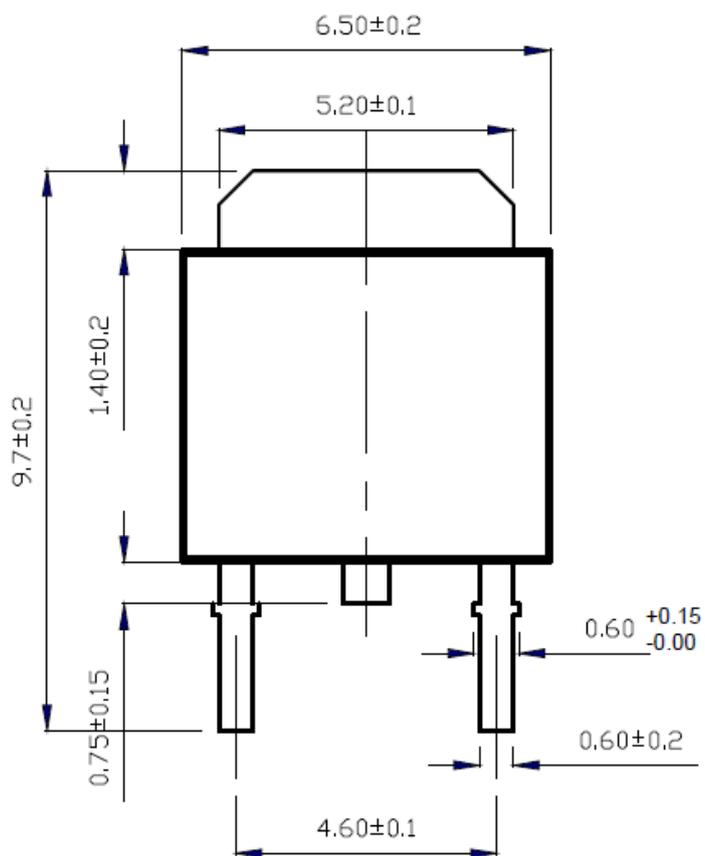
**TO-220F**



TO-251



TO-252



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  - b.support or sustain life,
  - c.whose failuer to when properly used in accordance with instructions for used provided in the laeling,can be reasonably expected to result in significant injury to the user.
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